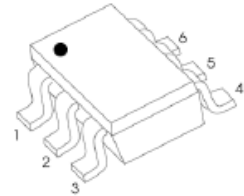
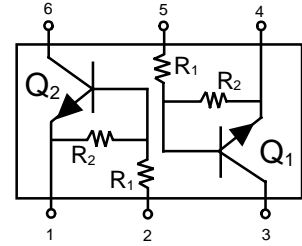


## Dual NPN Bias Resistor Transistors

### Dual Bias Resistor Transistors NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the SMUN5211DW, two BRT devices are housed in the SOT-363 package which is ideal for low power surface mount applications where board space is at a premium.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- We declare that the material of product compliance with RoHS requirements.



SOT-363

### DEVICE MARKING , RESISTOR VALUES AND ORDERING INFORMATION

Device	Package	Marking	R1(K)	R2(K)	Shipping
SMUN5211DW	SOT-363	7A	10	10	3000/Tape&Reel

### MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted, common for Q<sub>1</sub> and Q<sub>2</sub>)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current	I <sub>C</sub>	100	mAdc

### THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T <sub>A</sub> = 25°C	P <sub>D</sub>	187 (Note 1.) 256 (Note 2.)	mW
Derate above 25°C		1.5 (Note 1.) 2.0 (Note 2.)	mW/°C
Thermal Resistance – Junction-to-Ambient	R <sub>θJA</sub>	670 (Note 1.) 490 (Note 2.)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T <sub>A</sub> = 25°C	P <sub>D</sub>	250 (Note 1.) 385 (Note 2.)	mW
Derate above 25°C		2.0 (Note 1.) 3.0 (Note 2.)	mW/°C
Thermal Resistance – Junction-to-Ambient	R <sub>θJA</sub>	493 (Note 1.) 325 (Note 2.)	°C/W
Thermal Resistance – Junction-to-Lead	R <sub>θJL</sub>	188 (Note 1.) 208 (Note 2.)	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

1. FR-4 @ Minimum Pad      2. FR-4 @ 1.0 x 1.0 inch Pad

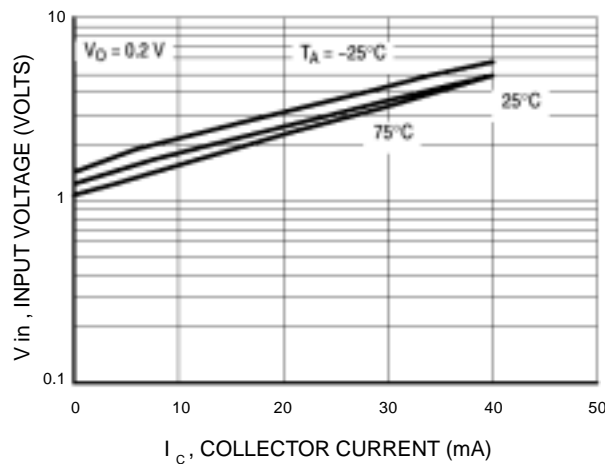
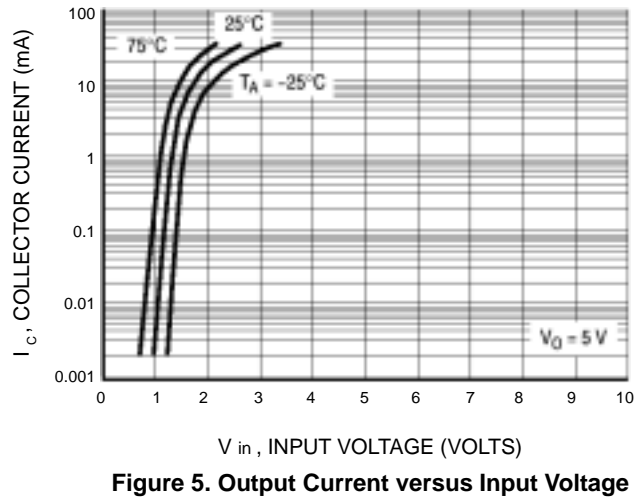
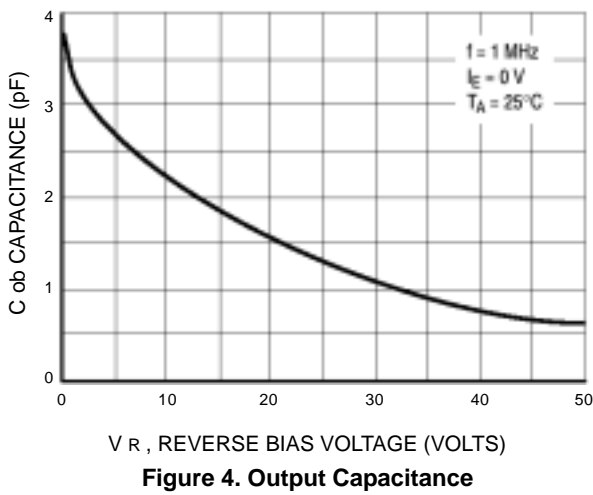
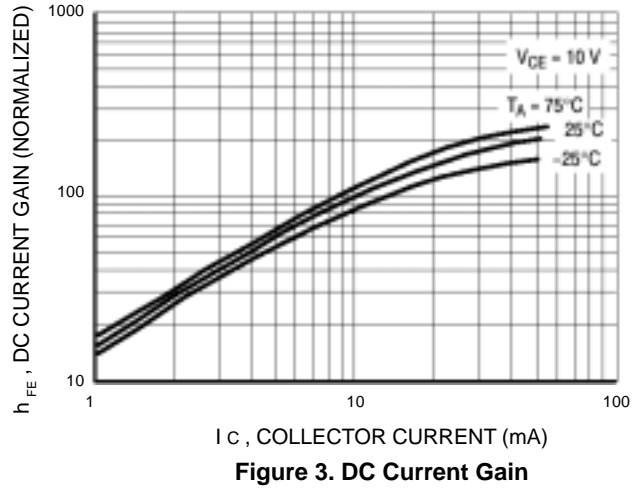
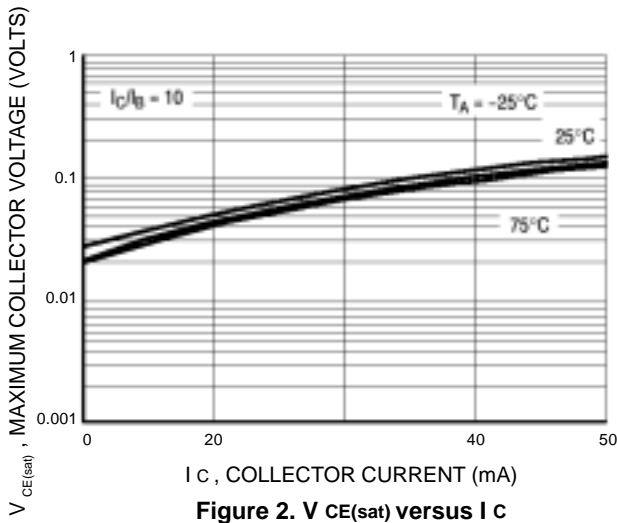
**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted, common for Q<sub>1</sub> and Q<sub>2</sub>),(Continued)

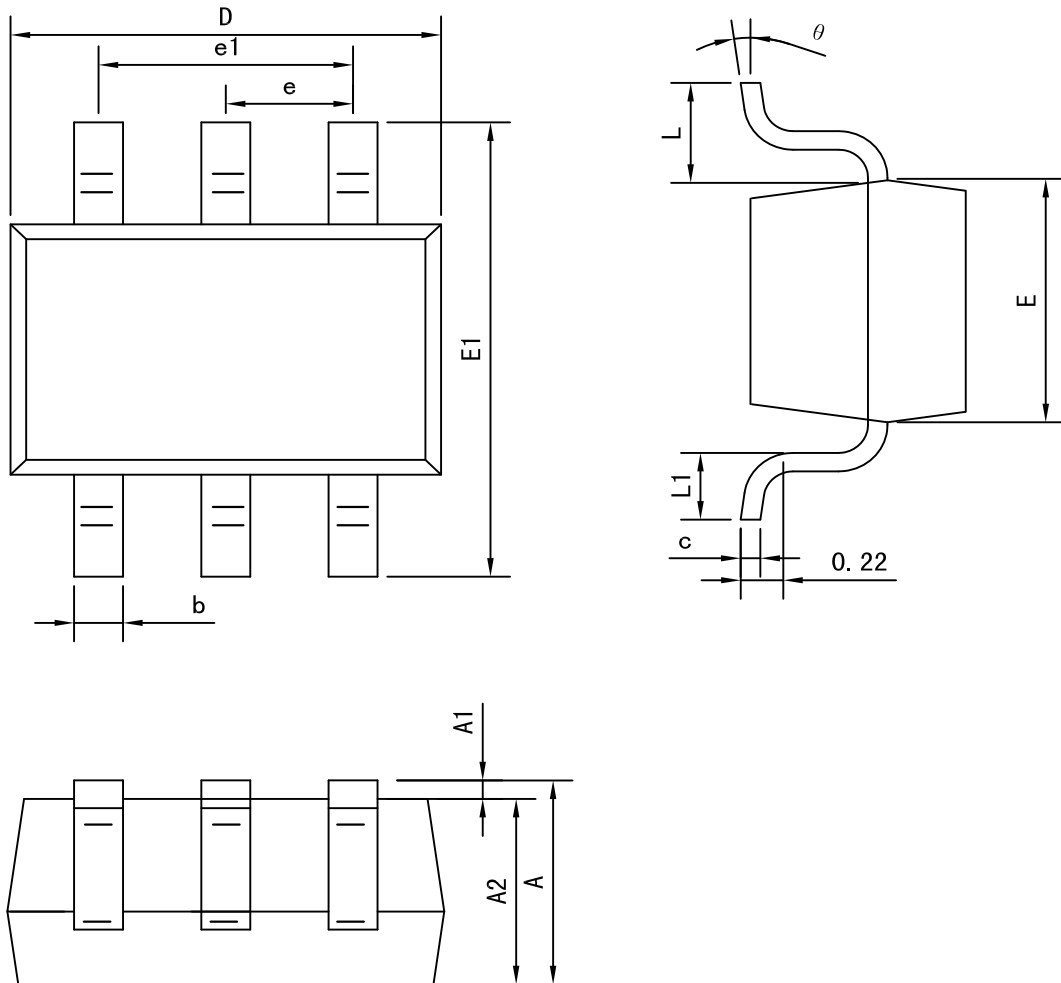
Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$ , $I_C = 5\text{ mA}$	$h_{FE}$	35	-	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	$I_{CBO}$	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 50\text{ V}$	$I_{CEO}$	-	500	nA
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	$I_{EBO}$	-	0.5	mA
Collector Base Breakdown Voltage at $I_C = 10\ \mu\text{A}$	$V_{(BR)CBO}$	50	-	V
Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$	$V_{(BR)CEO}$	50	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$ , $I_B = 0.3\text{ mA}$	$V_{CEsat}$	-	0.25	V

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted, common for Q<sub>1</sub> and Q<sub>2</sub>),(Continued)

Parameter	Symbol	Min.	Max.	Unit
Output Voltage (on) at $V_{CC} = 5\text{ V}$ , $V_B = 2.5\text{ V}$ , $R_L = 1\text{ K}\Omega$	$V_{OL}$	-	0.2	V
Output Voltage (off) at $V_{CC} = 5\text{ V}$ , $V_B = 0.5\text{ V}$ , $R_L = 1\text{ K}\Omega$	$V_{OH}$	4.9	-	V
Input Resistor	R1	7	13	K $\Omega$
Resistor Ratio	R1/R2	0.8	1.2	-

## TYPICAL ELECTRICAL CHARACTERISTICS



**SOT-363 Package outline dimensions**


Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
$\theta$	0°	8°